L Number	Hits	Search Text	DB	Time stamp
1	2369	((438/150) or (438/151) or (438/166) or (438/378) or (438/486) or (438/489) or (438/795)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:16
2	1155	laser near anneal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:17
3	16138	continuous near wave	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:18
4	12	activate near (ion near2 implanting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:19
5	23699	ion near2 implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:19
6	58	(laser near anneal) and (continuous near wave)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:25
7	14	((laser near anneal) and (continuous near wave)) and (ion near2 implanting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:25
8	7	(((438/150) or (438/151) or (438/166) or (438/378) or (438/486) or (438/489) or (438/795)).CCLS.) and (((laser near anneal) and (continuous near wave)) and (ion near2 implanting))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:26
9	110	(laser near anneal) and (ion near2 implanting)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:26
10	27	(((438/150) or (438/151) or (438/166) or (438/378) or (438/486) or (438/489) or (438/795)).CCLS.) and ((laser near anneal) and (ion near2 implanting))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/03 10:26
–	18	laser adj thermal adj anneal$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:02
–	3922	laser adj anneal$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:28
–	23	(laser adj anneal$3) with ((source and drain) adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:04
–	0	(laser adj anneal$3) with (continous adj puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:40

–	0	(laser adj anneal$3) with (mutli$3 adj puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:40
–	380	(laser adj anneal$3) with puls$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:30
–	33	((laser adj anneal$3) with puls$3) with continuous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:31
–	0	(laser adj anneal$3) with (continuous adj puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:04
–	3	(laser adj anneal$3) with (multi$3 adj puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 16:41
–	0	(laser adj anneal$3) near (continuous adj puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:01
–	7	(laser adj anneal$3) and (continuous adj puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:07
–	1	(laser adj anneal$3) with (continuous near puls$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:05
–	31584	ion adj implant$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:07
–	0	(ion adj implant$3) and (laser adj anneal$3 with (continuous or multi) adj pulse)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:27
–	0	(ion adj implant$3) and (laser adj anneal$3 with ((continuous or multi) adj pulse))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:10
–	1	(ion adj implant$3) and (laser adj anneal$3 and ((continuous or multi) adj pulse))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 17:13
–	1486	activat$3 with (ion adj implant$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:39
–	29	(activat$3 with (ion adj implant$3)) with (laser adj anneal$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:34

–	21	(laser adj substrate) with mov$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:44
–	0	((laser adj substrate) with mov$3) with (activat$3 with (ion adj implant$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:39
–	0	((laser adj substrate) with mov$3) and (activat$3 with (ion adj implant$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:39
–	0	((laser adj substrate) with mov$3) with activat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:51
–	147	(laser near substrate) with mov$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:51
–	11	((laser near substrate) with mov$3) and ion adj implant$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:45
–	2014	(laser with substrate) with mov$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:51
–	68	((laser with substrate) with mov$3) and ion adj implant$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:51
–	30	(((laser with substrate) with mov$3) and ion adj implant$4) and activat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 18:52